Solutions to $\it The \ Art \ of \ Electronics \ 3rd \ Edition$

February 18, 2024

Contents

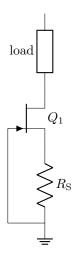
1	Solutions for Chapter 3		1.10 Exercise 3.10	
	1.1 Exercise 3.1	5	1.11 Exercise 3.11	10
	1.2 Exercise 3.2	5	1.12 Exercise 3.12	11
	1.3 Exercise 3.3		1.13 Exercise 3.13	12
	1.4 Exercise 3.4		1.14 Exercise 3.14	
	1.5 Exercise 3.5		1.15 Exercise 3.15	
	1.6 Exercise 3.6		1.16 Exercise 3.16 TODO: write solution	
	1.7 Exercise 3.7			
	1.8 Exercise 3.8		1.17 Exercise 3.17 TODO: write solution	
	1.9 Exercise 3.9	10	1.18 Exercise 3.18 TODO : write solution	- 13

4 CONTENTS

Solutions for Chapter 3

Exercise 3.1

Figure 1.1: JFET current source



From Figure 3.21 of the book, one can see that a drain current equal to $1\,\mathrm{mA}$ corresponds to a gate-source voltage of $-0.6\,\mathrm{V}$. Therefore:

$$R_{\rm S} = \frac{0.6\,\mathrm{V}}{1\,\mathrm{mA}} = 600\,\Omega$$

Exercise 3.2

At $V_{\text{GS}} = V_{\text{G0}}$:

$$r_{\mathrm{GS}} = r_{\mathrm{G0}} = \frac{1}{2k \left(V_{\mathrm{G0}} - V_{\mathrm{th}} \right)}$$

The ratio between $r_{\rm DS}$ and $R_{\rm G0}$ returns:

$$\frac{r_{\rm DS}}{r_{\rm G0}} = \frac{2k (V_{\rm G0} - V_{\rm th})}{2k (V_{\rm GS} - V_{\rm th})}$$

Being $g_{\rm m}$ the differential conductance of the FET operated in aturation region, it can be expressed as:

$$g_{\rm m} = \frac{\partial I_{\rm D}}{\partial V_{\rm GS}} = \frac{\partial}{\partial V_{\rm GS}} k \left(V_{\rm GS} - V_{\rm th} \right)^2 = 2k \left(V_{\rm GS} - V_{\rm th} \right)$$

Therefore:

$$g_{\rm m} = \frac{1}{r_{\rm DS}}$$

Exercise 3.4

(a) The voltage change across the drain-gate capacitance when the JFET is switched on $(V_{DS} = 0 \text{ V})$ is equal to 50 V - (0 V - 10 V) = 60 V. Considering a maximum current across this capacitance equal to 1 A:

$$t_{\rm ON} = \frac{60\,\mathrm{V}\,200\,\mathrm{pF}}{1\,\mathrm{A}} = 12\,\mathrm{ns}$$

(b) Since the current is equal to the charge over time, we have:

$$t_{\rm ON} = \frac{40\,\mathrm{nC}}{1\,\mathrm{A}} = 40\,\mathrm{ns}$$

Exercise 3.5

The 1 pF drain-source capacitance happens to be in series with the $10\,\mathrm{k}\Omega$ load resistance. The capacitive reactance is:

$$X_{\mathrm{DS}} = \frac{1}{2\pi 1\,\mathrm{MHz}\,1\,\mathrm{pF}} = 160\,\mathrm{k}\Omega$$

Therefore, the feedthrough is given by:

$$20\log_{10}\frac{10\,\mathrm{k}\Omega}{10\,\mathrm{k}\Omega + 160\,\mathrm{k}\Omega} = -25\,\mathrm{dB}$$

Exercise 3.6

In this case, the output $10 \,\mathrm{k}\Omega$ resistance is in parallel with the $50 \,\Omega$ R_{ON} resistance. Their equivalent resistance is about $50 \,\Omega$. Similarly to the previous exercise, the feedthorugh is given by:

$$20\log_{10}\frac{50\,\Omega}{50\,\Omega + 160\,\mathrm{k}\Omega} = -70\,\mathrm{dB}$$

1.7. EXERCISE 3.7

Exercise 3.7

Figure 1.2: Zero ohm $R_{\rm ON}$

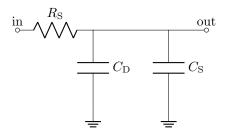
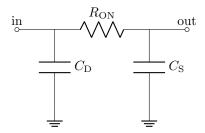


Figure 1.3: $75 \Omega R_{ON}$



For this exercise we assume that the load resistance of $100\,\mathrm{k}\Omega$ does not load the circuit.

(a) The circuit is that of Figure 1.2. Since $C_D = C_S = C_T = 8 \,\mathrm{pF}$, there is a single pole at the frequency f_P :

$$\boxed{f_{\rm p} = \frac{1}{4\pi R_{\rm S} C_{\rm T}} \approx 1\,{\rm MHz}}$$

(b) In this case the circuit is depicted in Figure 1.3. The circuit has one pole at DC and another pole at $f_{\rm p}$:

$$\boxed{f_{\rm p} = \frac{1}{2\pi R_{\rm ON} C_{\rm T}} \approx 265\,{\rm MHz}}$$

Figure 1.4: OFF-OFF

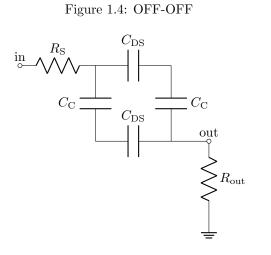
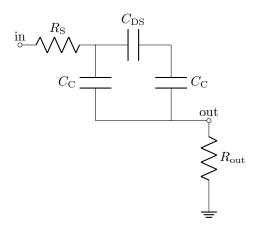


Figure 1.5: OFF-ON



1.8. EXERCISE 3.8

Figure 1.6: ON-OFF

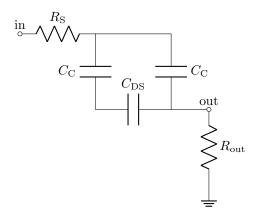
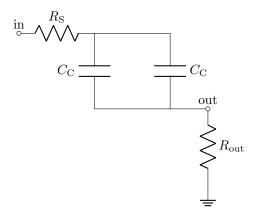


Figure 1.7: ON-ON



(a) In this case the reference circuit is depicted in Figure 1.4. The cross-coupling is given by:

$$20 \log_{10} \frac{R_{\text{out}}}{R_{\text{out}} + R_{\text{S}} + 0.5(X_{\text{C}} + X_{\text{DS}})} = -10.75 \,\text{dB}$$

being
$$X_{\rm C}=\frac{1}{2\pi f\,C_{\rm C}}=320\,{\rm k}\Omega$$
 and $X_{\rm DS}=\frac{1}{2\pi f\,C_{\rm DS}}=160\,{\rm k}\Omega$

(b) In this case the reference circuit is depicted in Figure 1.5. The cross-coupling is given by:

$$20\log_{10}\frac{R_{\text{out}}}{R_{\text{out}} + R_{\text{S}} + \frac{X_{\text{C}}(X_{\text{C}} + X_{\text{DS}})}{2X_{\text{C}} + X_{\text{DS}}}} = -9.6\,\text{dB}$$

- (c) In this case the reference circuit is depicted in Figure 1.6. The cross-coupling is the same as before
- (d) In this case the reference circuit is depicted in Figure 1.7. The cross-coupling is given by:

$$20\log_{10}\frac{R_{\text{out}}}{R_{\text{out}} + R_{\text{S}} + 0.5X_{\text{C}}} = -8.6\,\text{dB}$$

(a) Considering the different combinations of resistors, the $-3\,\mathrm{dB}$ frequencies can be computed as:

$$f_{\rm 3dB,n} = \frac{n G_{\rm 10k}}{2\pi C} \quad n = 1 \dots 15$$

where $C = 0.01 \,\mu\text{F}$ and $G_{10k} = 0.1 \,\text{mS}$

(b) The glitch amplitude voltage can be computed as:

$$\Delta V = \frac{20 \,\mathrm{pC}}{C} = 2 \,\mathrm{mV}$$

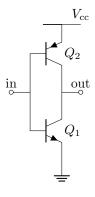
Exercise 3.10

The peak output current that the buffer has to provide can be given as the peak time derivative of the output voltage across the 10 nF capacitor multiplied by its value:

$$\boxed{I_{\rm p} = 10\,{\rm nF} \frac{dV}{dt}\bigg|_{\rm p} = 10\,{\rm nF}\,2\pi 10\,{\rm kHz}\,1\,{\rm V} = 0.6\,{\rm mA}}$$

Exercise 3.11

Figure 1.8: BJT-based inverter logic circuit



The circuit of Figure 1.8 represents the complementary bjt inverter. It's easy to see that without a proper bias, if the input is grounder (low level) the $V_{\rm BE}$ of the pnp transistor is equal to $V_{\rm cc}$ which is likely to damage the transistor in a very short time

1.12. EXERCISE 3.12

Exercise 3.12

Figure 1.9: Logic AND symbols

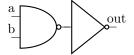
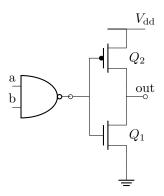
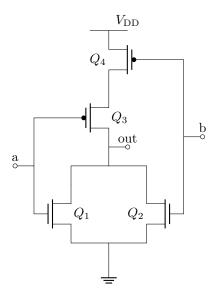


Figure 1.10: Logic AND symbol and circuit



In order to transform a NAND port into an AND port, we can use a NOT port as shown in Figures 1.9 and 1.10

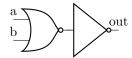
Figure 1.11: NOR circuit



The solution is presented in Figure 1.11

Exercise 3.14

Figure 1.12: Logic OR symbols

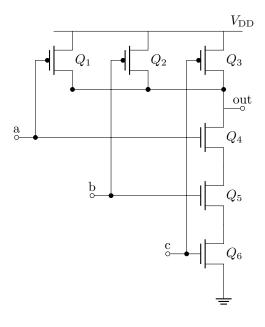


The OR circuit can be easily obtained by cascading a NOT circuit to the NOR circuit designed in exercise 3.13.

1.15. EXERCISE 3.15

Exercise 3.15

Figure 1.13: Three ports NAND circuit



The solution is represented in Figure 1.13. The gate comply with the following truth table

a	b	\mathbf{c}	out
1	1	1	0
1	1	0	1
1	0	0	1
1	0	1	1
0	0	1	1
0	1	0	1
0	1	1	1
0	0	0	1

Exercise 3.16 TODO: write solution

Exercise 3.17 TODO: write solution

Exercise 3.18 TODO: write solution